Accepted Manuscript

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PII:	S0040-6090(18)30185-8
DOI:	doi:10.1016/j.tsf.2018.03.041
Reference:	TSF 36545
To appear in:	Thin Solid Films
Received date:	9 December 2017
Revised date:	10 March 2018
Accepted date:	14 March 2018

Please cite this article as: Jaeyoung Kim, Seungbeom Choi, Jeong-Wan Jo, Sung Kyu Park, Yong-Hoon Kim, Solution-processed lanthanum-doped Al2O3 gate dielectrics for high-mobility metal-oxide thin-film transistors. The address for the corresponding author was captured as affiliation for all authors. Please check if appropriate. Tsf(2017), doi:10.1016/j.tsf.2018.03.041

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ACCEPTED MANUSCRIPT

Solution-Processed Lanthanum-doped Al₂O₃ Gate Dielectrics for High-Mobility

Metal-Oxide Thin-Film Transistors

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